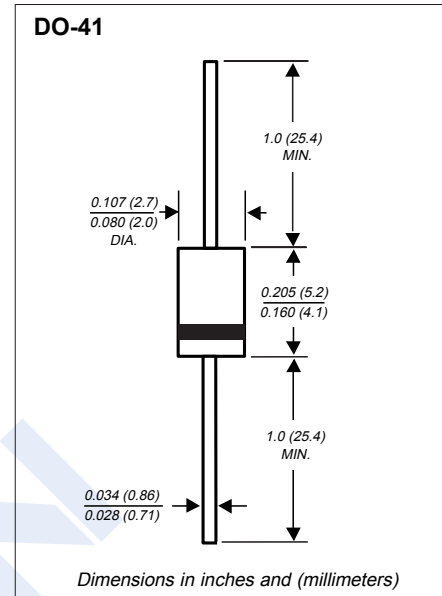


Schottky Diodes

SR120 ~ SR1100

■ Features

- Schottky Barrier Chip
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	SR120	SR130	SR140	SR150	SR160	SR180	SR1100	Unit	
Repetitive Peak Reverse Voltage	V_{RRM}	20	30	40	50	60	80	100	V	
Working Peak Reverse Voltage	V_{RWM}									
Maximum DC Blocking Voltage	V_{DC}									
RMS Reverse Voltage	$V_{R(RMS)}$	14	21	28	35	42	56	70		
Forward Voltage	V_F	0.5			0.7		0.85			
Average Rectified Output Current @ $T_L=100^\circ\text{C}$	I_o	1								A
Peak Forward Surge Current @ 8.3ms	I_{FSM}	40								
Maximum DC Reverse Current $T_a=25^\circ\text{C}$ $T_a=100^\circ\text{C}$	I_R	0.5				10				mA
Typical Junction Capacitance (Note.1)	C_j	110			80					pF
Thermal Resistance.Junction- to-Ambient	R_{thJA}	50								$^\circ\text{C}/\text{W}$
Thermal Resistance.Junction- to-Lead	R_{thJL}	15								
Junction Temperature	T_j	150								$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to 150								

Note.1 Measured at 1MHz and applied reverse voltage of 4V D.C

Schottky Diodes

SR120 ~ SR1100

Typical Characteristics

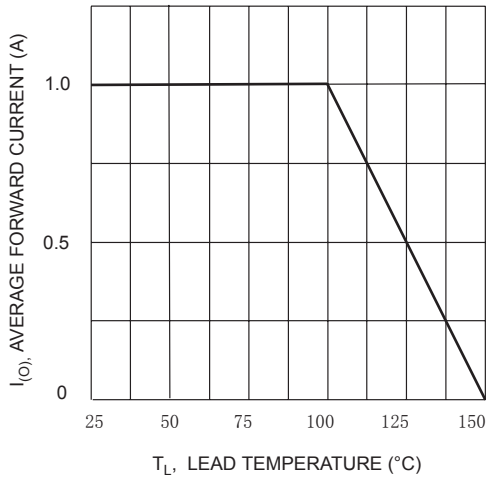


Fig. 1 Forward Current Derating Curve

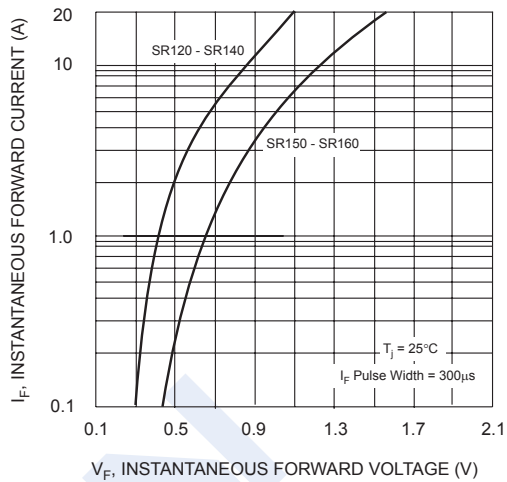


Fig. 2 Typical Forward Characteristics

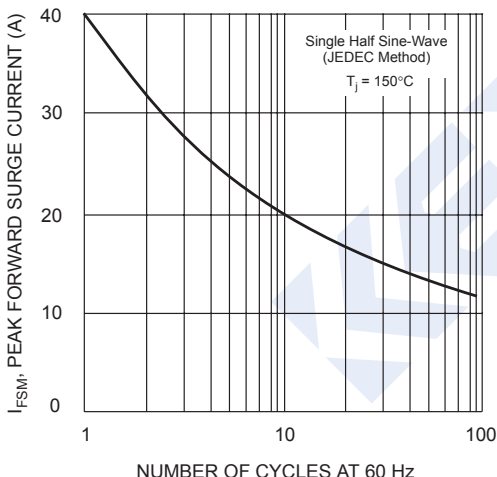


Fig. 3 Max Non-Repetitive Peak Fwd Surge Current

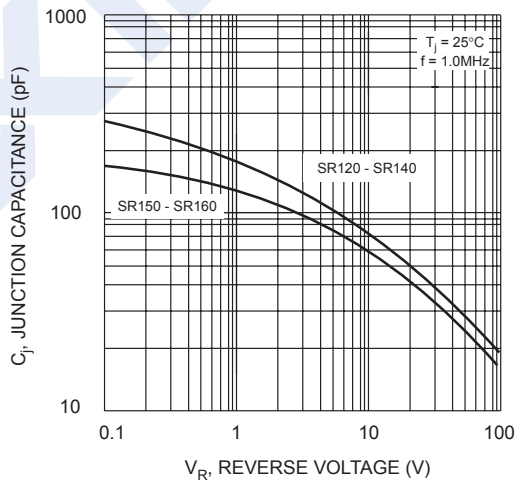


Fig. 4 Typical Junction Capacitance

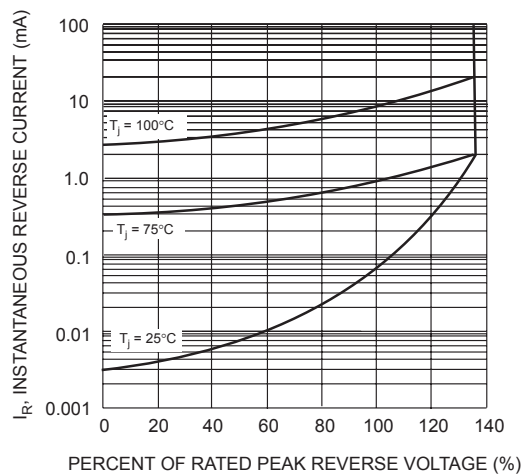


Fig. 5 Typical Reverse Characteristics